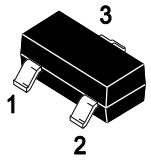
LMBT3904LT1G

General Purpose Transistors NPN Silicon



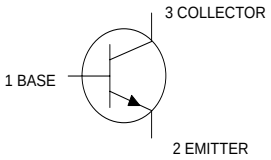
SOT23(TO-236)

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.

2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LMBT3904LT1G	1AM	3000/Tape&Reel
LMBT3904LT3G	1AM	13000/Tape&Reel



3. MAXIMUM RATINGS(Ta = 25ºC)

Parameter	Symbol	Limits	Unit
Collector–Emitter Voltage	VCEO	40	V
Collector–Base Voltage	VCBO	60	V
Emitter–Base Voltage	VEBO	6	V
Collector Current — Continuous	IC	200	mA

4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation,	PD		
FR−5 Board (Note 1) @ TA = 25ºC		225	mW
Derate above 25ºC		1.8	mW/ºC
Thermal Resistance,			
Junction–to–Ambient(Note 1)	RΘJA	556	ºC/W
Junction–to–Case(Note 1)	RΘJC	300	ºC/W
Junction and Storage temperature	TJ,Tstg	−55~+150	° C

1. FR–5 = 1.0×0.75×0.062 in.

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage (IC = 1.0 mA, IB = 0)	VBR(CEO)	40	-	-	V
Collector–Base Breakdown Voltage (IC = 10 μA, IE = 0)	VBR(CBO)	60	-	-	V
Emitter–Base Breakdown Voltage (IE = 10 μA, IC = 0)	VBR(EBO)	6	-	-	V
Collector Cutoff Current (VCE = 30 V, VEB = 3.0V)	ICEX	-	-	50	nA
Base Cutoff Current (VCE = 30 Vdc, VEB = 3.0Vdc)	IBL	-	-	50	nA

ON CHARACTERISTICS (Note 2.)

DC Current Gain	HFE				
(IC = 0.1 mA, VCE = 1.0 V)		40	-	-	
(IC = 1.0 mA, VCE = 1.0 V)		70	-	-	
(IC = 10 mA, VCE = 1.0 V)		100	-	300	
(IC = 50 mA, VCE = 1.0 V)		60	-	-	
(IC = 100 mA, VCE = 1.0 V)		30	-	-	
Collector–Emitter Saturation Voltage	VCE(sat)				V
(IC = 10 mA, IB = 1.0 mA)		-	-	0.2	
(IC = 50 mA, IB = 5.0 mA)		-	-	0.3	
Base–Emitter Saturation Voltage	VBE(sat)				V
(IC = 10 mA, IB = 1.0 mA)		-	-	0.85	
(IC = 50 mA, IB = 5.0 mA)		-	-	0.95	

SMALL–SIGNAL CHARACTERISTICS

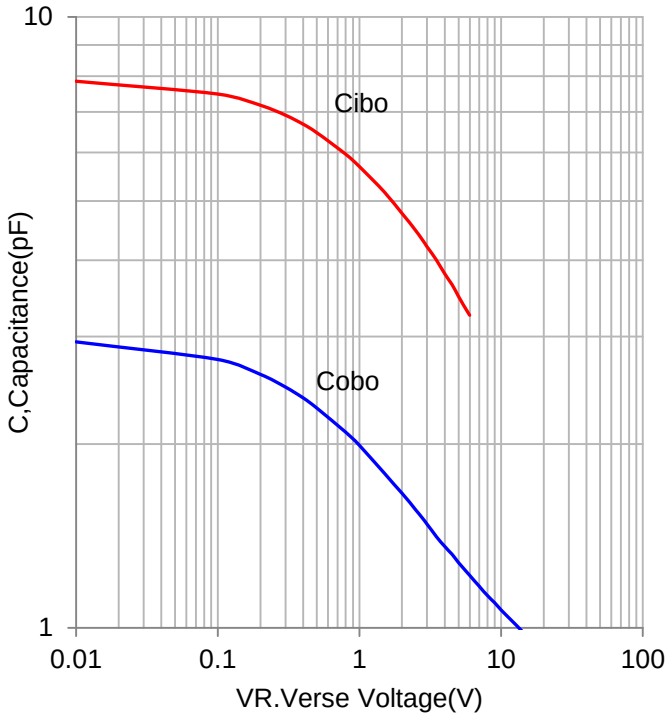
Current–Gain — Bandwidth Product (IC = 10mA, VCE= 20V, f = 100MHz)	fT	300	-	-	MHz
Output Capacitance (VCB = 5.0 V, IE = 0, f = 1.0 MHz)	Cobo	-	-	4	pF
Input Capacitance (VEB = 0.5 V, IC = 0, f = 1.0 MHz)	Cibo	-	-	8	pF

SWITCHING CHARACTERISTICS

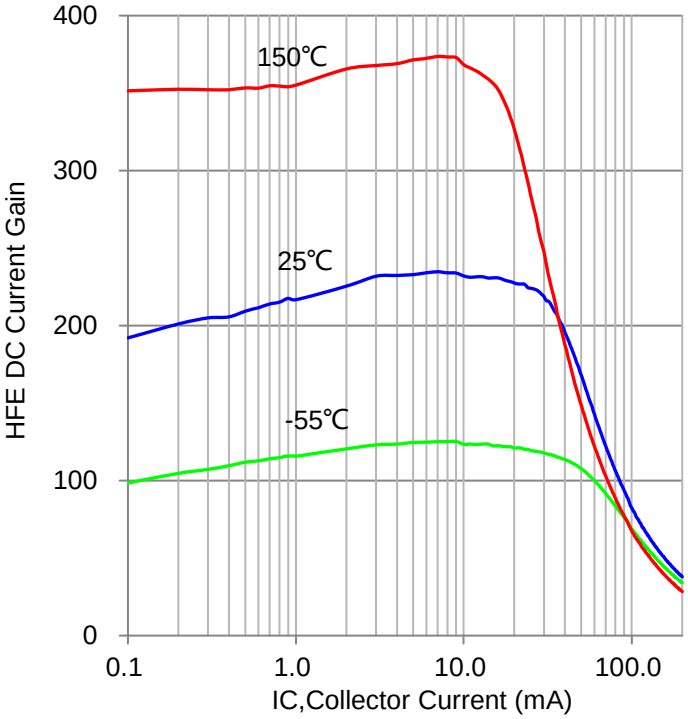
Delay Time	(VCC = 3.0 V,VBE=-0.5V, IC = 10mA, IB1 = 1.0 mA)	td	-	-	35	ns
Rise Time		tr	-	-	35	
Storage Time	(VCC = 3.0 V, IC = 10 mA,IB1 = IB2 = 1.0 mA)	ts	-	-	200	
Fall Time		tf	-	-	50	

2.Pulse Test: Pulse Width ≤300 μs, Duty Cycle ≤2.0%.

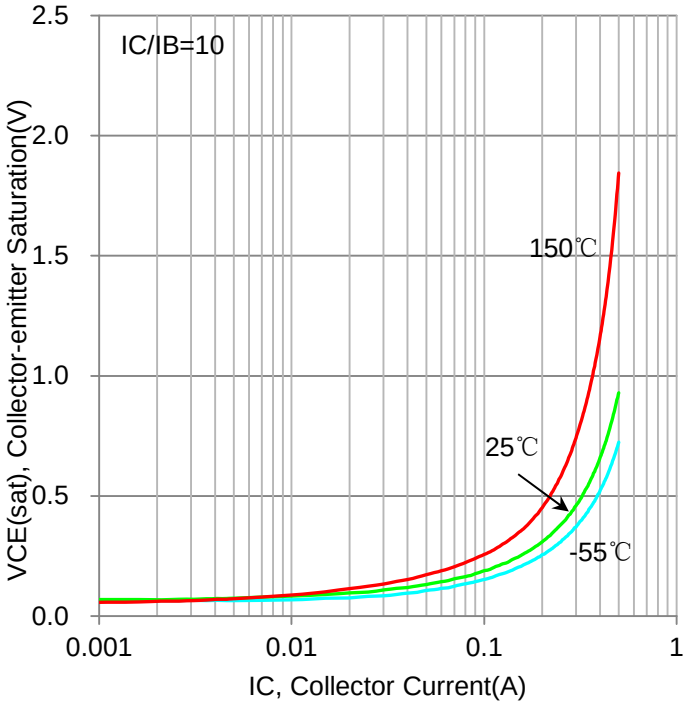
6. ELECTRICAL CHARACTERISTICS CURVES



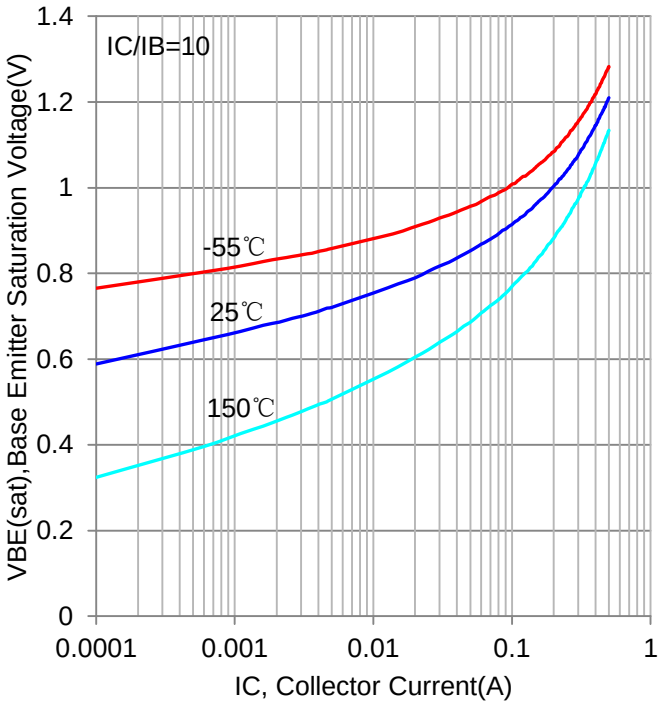
Capacitance



DC Current Gain

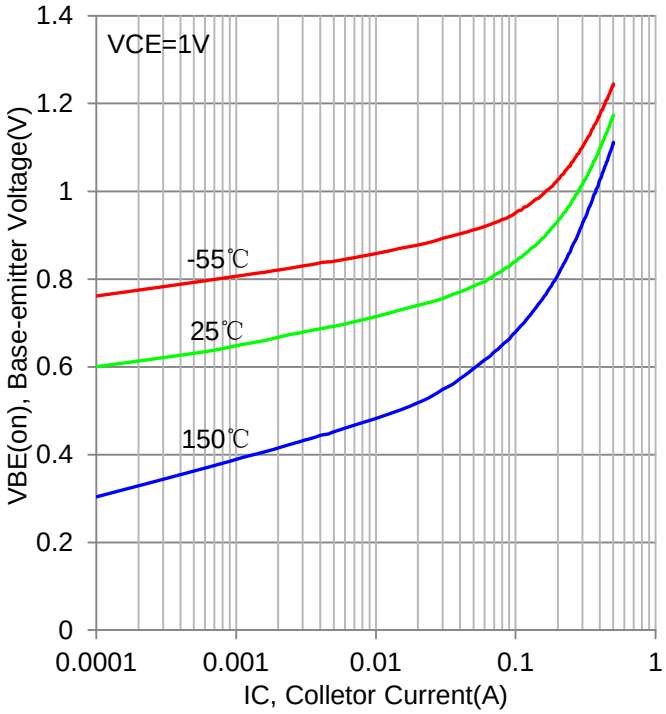


VCE(sat) vs. IC

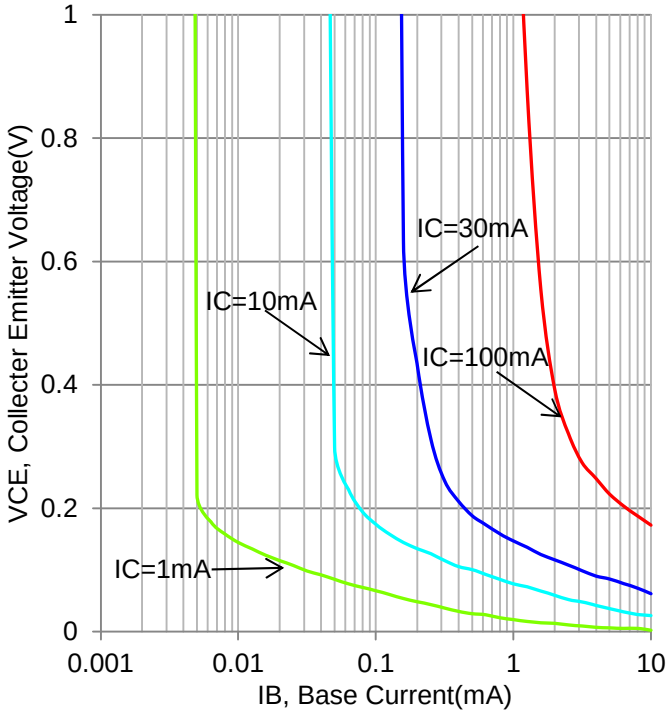


VBE(sat) vs. IC

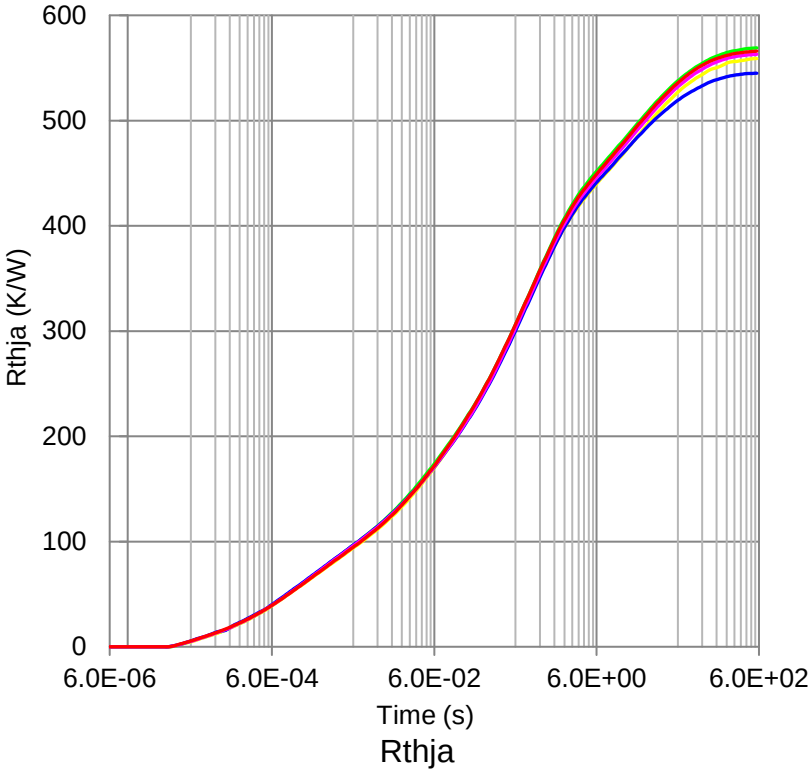
6. ELECTRICAL CHARACTERISTICS CURVES(Con.)



VBE(on) vs. IC

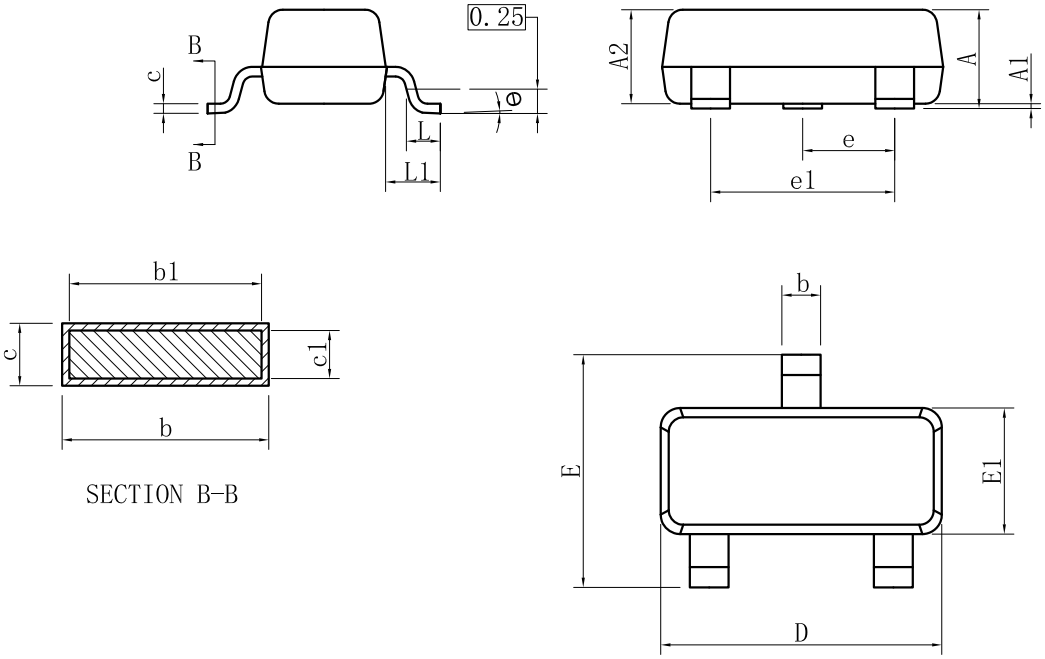


Collector Saturation Region



Rthja

7.OUTLINE AND DIMENSIONS

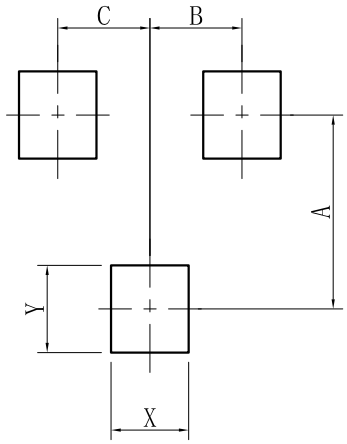


SOT23			
DIM	MIN	NOR	MAX
A	0.89	-	1.12
A1	0.01	-	0.10
A2	0.88	0.95	1.02
b	0.30	-	0.50
b1	0.30	0.40	0.45
c	0.08	-	0.20
c1	0.08	0.10	0.16
D	2.80	2.90	3.04
E	2.10	-	2.64
E1	1.20	1.30	1.40
e	0.95BSC		
e1	1.90BSC		
L	0.40	0.46	0.60
L1	0.54REF		
θ	0°	-	8°
All Dimensions in mm			

GENERAL NOTES

1. Top package surface finish Ra0.4±0.2um
2. Bottom package surface finish Ra0.7±0.2um
3. Side package surface finish Ra0.4±0.2um

8.SOLDERING FOOTPRINT



SOT-23	
DIM	(mm)
X	0.80
Y	0.90
A	2.00
B	0.95
C	0.95

DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.

- Before you use our Products for new Project, you are requested to carefully read this document and fully under--stand its contents. LRC shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of any LRC’s Products against warning, caution or note contained in this document.

- All information contained in this document is current as of the issuing date and subject to change without any prior notice. Before purchasing or using LRC's Products,please confirm the latest information with a LRC sales represe--ntative.